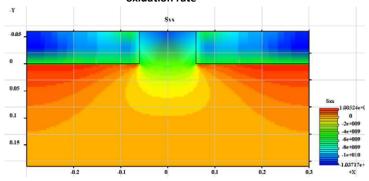


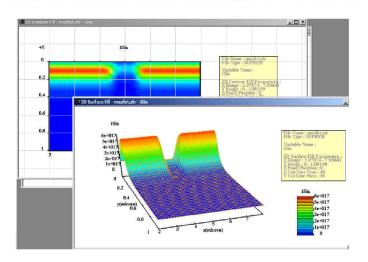
- Extension of Stanford code to 3D.
- Non-uniform temperature annealing.
- Data interface to Crosslight/Apsys simulator.
- Local heating profile imported from APSYS.
- Interface to Monte-Carlo implant simulator.
- Capability of CSuprem extended to compound devices:
 - Deposition/Etching model adapted to model complex electrode design of light-emitting diode (LED).
 - 2. Strain/stress analysis applied to MQW GaN LED growth.

CSuprem Capabilities:

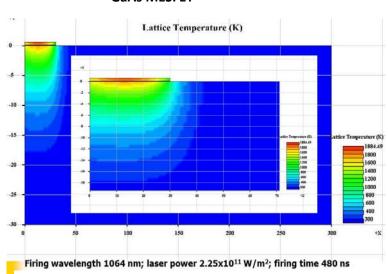
- Ion Implantation
 - Physical model
 - Damage model
 - Tilt model
- Anisotropic and Sacrificial Etching
- Deposition
- Diffusion
- Point defect based
- Paired and unpaired diffusion of point defects models
- Transient enhanced diffusion (TED) for damage and clustering
- Rapid Thermal Anneal
- Oxidation
- Dry oxidation
- Wet oxidation
- Effect of HCI, Orientation on oxidation rate
- Effect of doping level and pressure on oxidation rate



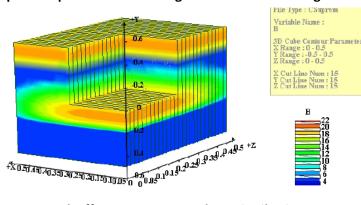
SiGe Stress Simulation



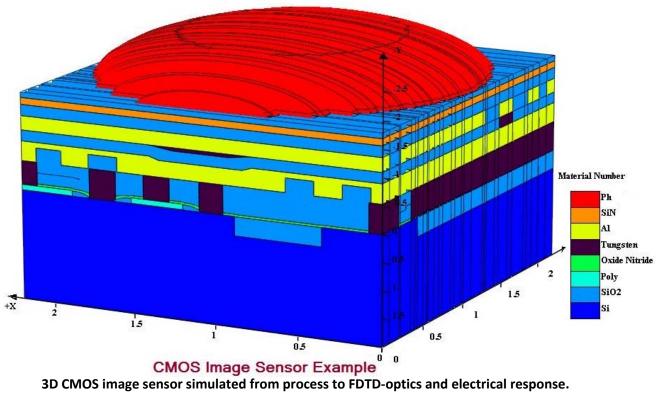
GaAs MESFET

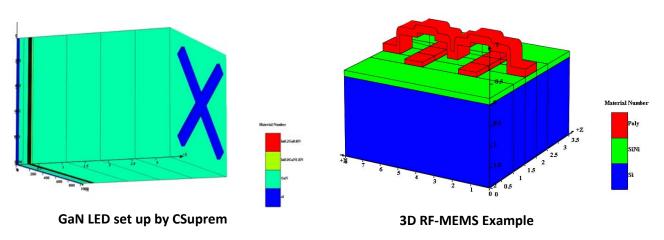


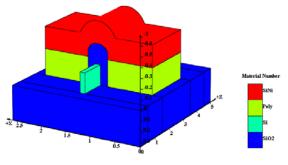
Non-uniform temperature profile generated by laser beam pulse imported from Crosslight APSYS for annealing.



3D Mask Effects on Boron Implant Distribution











URL: http://www.crosslight.com e-mail: info@crosslight.com